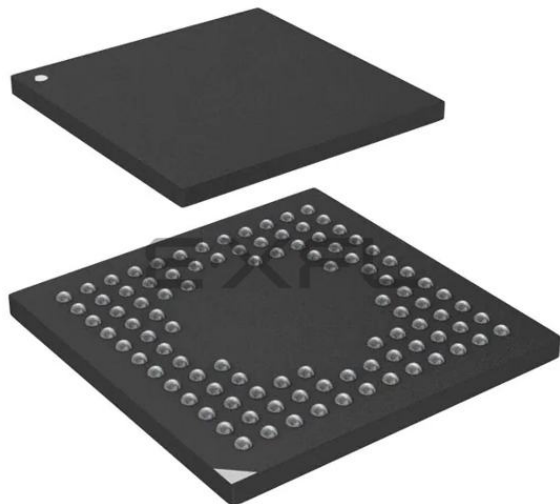




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Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	83
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA
Supplier Device Package	100-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152vbh6a

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L151x6/8/B-A and STM32L152x6/8/B-A ultra-low-power ARM® Cortex®-M3 based microcontrollers product line.

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A microcontroller family includes devices in 3 different package types: from 48 to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, Wired and wireless sensors, Video intercom
- Utility metering

This STM32L151x6/8/B-A and STM32L152x6/8/B-A datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The document "Getting started with STM32L1xxxx hardware development" AN3216 gives a hardware implementation overview.

Both documents are available from the STMicroelectronics website www.st.com.

For information on the ARM® Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the ARM website.

Figure 1 shows the general block diagram of the device family.

Caution: This datasheet does not apply to:
– STM32L15xx6/8/B
covered by a separate datasheet.

3.1 Low-power modes

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices support dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply:

- In Range 1 (V_{DD} range limited to 1.71-3.6 V), the CPU runs at up to 32 MHz (refer to [Table 18](#) for consumption).
- In Range 2 (full V_{DD} range), the CPU runs at up to 16 MHz (refer to [Table 18](#) for consumption)
- In Range 3 (full V_{DD} range), the CPU runs at up to 4 MHz (generated only with the multispeed internal RC oscillator clock source). Refer to [Table 18](#) for consumption.

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
Sleep mode power consumption: refer to [Table 20](#).
- **Low-power Run mode**
This mode is achieved with the multispeed internal (MSI) RC oscillator set to the minimum clock (less than 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In the low-power Run mode, the clock frequency and the number of enabled peripherals are both limited.
Low-power Run mode consumption: refer to [Table 21](#).
- **Low-power Sleep mode**
This mode is achieved by entering the Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In the low-power Sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.
When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.
Low-power Sleep mode consumption: refer to [Table 22](#).
- **Stop mode with RTC**
Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.
The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.
- **Stop mode without RTC**
Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode.
The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

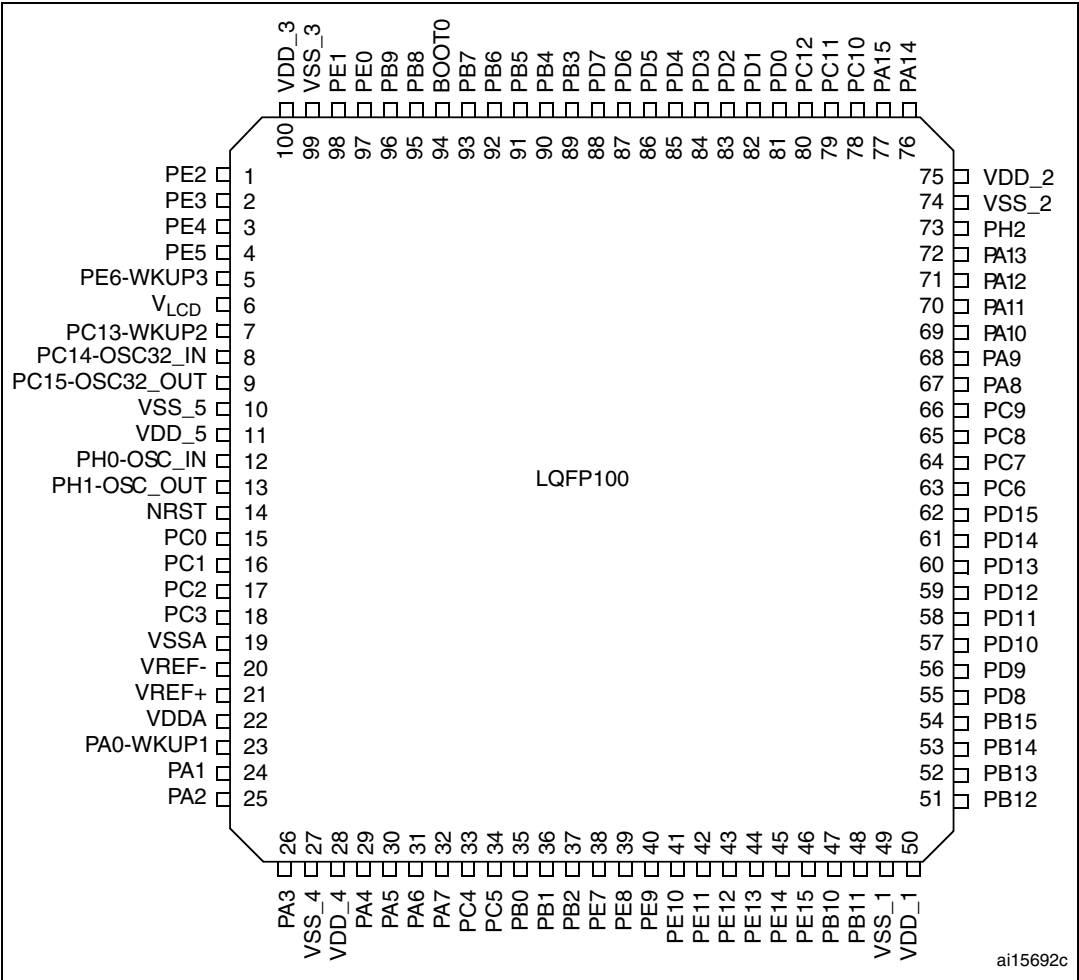
3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System Memory
- Boot from embedded RAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1 or USART2. See the application note “STM32 microcontroller system memory boot mode” (AN2606) for details.

Figure 4. STM32L15xVxxxA LQFP100 pinout



1. This figure shows the package top view.

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UQFPN48					Alternate functions	Additional functions
35	26	F5	M5	18	PB0	I/O	TC	PB0	TIM3_CH3/ LCD_SEG5	ADC_IN8/ COMP1_INP/ VREF_OUT /VLCDRAIL3
36	27	G5	M6	19	PB1	I/O	FT	PB1	TIM3_CH4/ LCD_SEG6	ADC_IN9/ COMP1_INP/ VREF_OUT
37	28	G6	L6	20	PB2	I/O	FT	PB2/ BOOT1	BOOT1	VLCDRAIL1
38	-	-	M7	-	PE7	I/O	TC	PE7	-	ADC_IN22/ COMP1_INP
39	-	-	L7	-	PE8	I/O	TC	PE8	-	ADC_IN23/ COMP1_INP
40	-	-	M8	-	PE9	I/O	TC	PE9	TIM2_CH1_ETR	ADC_IN24/ COMP1_INP
41	-	-	L8	-	PE10	I/O	TC	PE10	TIM2_CH2	ADC_IN25/ COMP1_INP
42	-	-	M9	-	PE11	I/O	FT	PE11	TIM2_CH3	VLCDRAIL2
43	-	-	L9	-	PE12	I/O	FT	PE12	TIM2_CH4/ SPI1_NSS	VLCDRAIL3
44	-	-	M10	-	PE13	I/O	FT	PE13	SPI1_SCK	-
45	-	-	M11	-	PE14	I/O	FT	PE14	SPI1_MISO	-
46	-	-	M12	-	PE15	I/O	FT	PE15	SPI1_MOSI	-
47	29	G7	L10	21	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX /TIM2_CH3/ LCD_SEG10	-
48	30	H7	L11	22	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX /TIM2_CH4/ LCD_SEG11	-
49	31	D6	F12	23	V _{SS_1}	S	-	V _{SS_1}	-	-
50	32	E6	G12	24	V _{DD_1}	S	-	V _{DD_1}	-	-

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions (continued)

Pins					Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
51	33	H8	L12	25	PB12	I/O	FT	PB12	SPI2_NSS/I2C2_SMBA/ USART3_CK/ LCD_SEG12/ TIM10_CH1	ADC_IN18/ COMP1_INP /VLCDRAIL2
52	34	G8	K12	26	PB13	I/O	FT	PB13	SPI2_SCK/ USART3_CTS/ LCD_SEG13/TIM9_CH1	ADC_IN19/ COMP1_INP
53	35	F8	K11	27	PB14	I/O	FT	PB14	SPI2_MISO/ USART3_RTS/ LCD_SEG14/TIM9_CH2	ADC_IN20/ COMP1_INP
54	36	F7	K10	28	PB15	I/O	FT	PB15	SPI2_MOSI/ LCD_SEG15/ TIM11_CH1	ADC_IN21/ COMP1_INP/ RTC_REFIN
55	-	-	K9	-	PD8	I/O	FT	PD8	USART3_TX/ LCD_SEG28	-
56	-	-	K8	-	PD9	I/O	FT	PD9	USART3_RX/ LCD_SEG29	-
57	-	-	J12	-	PD10	I/O	FT	PD10	USART3_CK/ LCD_SEG30	-
58	-	-	J11	-	PD11	I/O	FT	PD11	USART3_CTS/ LCD_SEG31	-
59	-	-	J10	-	PD12	I/O	FT	PD12	TIM4_CH1/ USART3_RTS/ LCD_SEG32	-
60	-	-	H12	-	PD13	I/O	FT	PD13	TIM4_CH2/LCD_SEG33	-
61	-	-	H11	-	PD14	I/O	FT	PD14	TIM4_CH3/LCD_SEG34	-
62	-	-	H10	-	PD15	I/O	FT	PD15	TIM4_CH4/LCD_SEG35	-
63	37	F6	E12	-	PC6	I/O	FT	PC6	TIM3_CH1/LCD_SEG24	-
64	38	E7	E11	-	PC7	I/O	FT	PC7	TIM3_CH2/LCD_SEG25	-
65	39	E8	E10	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
66	40	D8	D12	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	AFIO9	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART1/2/3	N/A	N/A	LCD	N/A	N/A	RI	SYSTEM
PB4	NJTRST	-	TIM3_CH1	-	-	SPI1_MISO	-	-	-	-	[SEG8]	-	-	-	EVENTOUT
PB5	-	-	TIM3_CH2	-	I2C1_SMBA	SPI1_MOSI	-	-	-	-	[SEG9]	-	-	-	EVENTOUT
PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	-	-	-	-	-	EVENTOUT
PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	-	-	-	-	EVENTOUT
PB8	-	-	TIM4_CH3	TIM10_CH1*	I2C1_SCL	-	-	-	-	-	SEG16	-	-	-	EVENTOUT
PB9	-	-	TIM4_CH4	TIM11_CH1*	I2C1_SDA	-	-	-	-	-	[COM3]	-	-	-	EVENTOUT
PB10	-	TIM2_CH3	-	-	I2C2_SCL	-	-	USART3_TX	-	-	SEG10	-	-	-	EVENTOUT
PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	SEG11	-	-	-	EVENTOUT
PB12	-	-	-	TIM10_CH1	I2C2_SMBA	SPI2_NSS	-	USART3_CK	-	-	SEG12	-	-	-	EVENTOUT
PB13	-	-	-	TIM9_CH1	-	SPI2_SCK	-	USART3_CTS	-	-	SEG13	-	-	-	EVENTOUT
PB14	-	-	-	TIM9_CH2	-	SPI2_MISO	-	USART3_RTS	-	-	SEG14	-	-	-	EVENTOUT
PB15	-	-	-	TIM11_CH1	-	SPI2_MOSI	-	-	-	-	SEG15	-	-	-	EVENTOUT
PC0	-	-	-	-	-	-	-	-	-	-	SEG18	-	-	TIMx_IC1	EVENTOUT
PC1	-	-	-	-	-	-	-	-	-	-	SEG19	-	-	TIMx_IC2	EVENTOUT
PC2	-	-	-	-	-	-	-	-	-	-	SEG20	-	-	TIMx_IC3	EVENTOUT
PC3	-	-	-	-	-	-	-	-	-	-	SEG21	-	-	TIMx_IC4	EVENTOUT
PC4	-	-	-	-	-	-	-	-	-	-	SEG22	-	-	TIMx_IC1	EVENTOUT
PC5	-	-	-	-	-	-	-	-	-	-	SEG23	-	-	TIMx_IC2	EVENTOUT
PC6	-	-	TIM3_CH1	-	-	-	-	-	-	-	SEG24	-	-	TIMx_IC3	EVENTOUT
PC7	-	-	TIM3_CH2	-	-	-	-	-	-	-	SEG25	-	-	TIMx_IC4	EVENTOUT
PC8	-	-	TIM3_CH3	-	-	-	-	-	-	-	SEG26	-	-	TIMx_IC1	EVENTOUT
PC9	-	-	TIM3_CH4	-	-	-	-	-	-	-	SEG27	-	-	TIMx_IC2	EVENTOUT

Table 23. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions			Typ ⁽¹⁾	Max ⁽¹⁾⁽²⁾	Unit
I_{DD} (Stop with RTC)	Supply current in Stop mode with RTC enabled	RTC clocked by LSI, regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	$T_A = -40^{\circ}\text{C}$ to 25°C $V_{DD} = 1.8\text{ V}$	1.13	-	μA
				$T_A = -40^{\circ}\text{C}$ to 25°C	1.38	4	
				$T_A = 55^{\circ}\text{C}$	1.70	6	
				$T_A = 85^{\circ}\text{C}$	3.30	10	
				$T_A = 105^{\circ}\text{C}$	7.80	23	
			LCD ON (static duty) ⁽³⁾	$T_A = -40^{\circ}\text{C}$ to 25°C	1.50	6	
				$T_A = 55^{\circ}\text{C}$	1.80	7	
				$T_A = 85^{\circ}\text{C}$	3.45	12	
				$T_A = 105^{\circ}\text{C}$	8.02	27	
		LCD ON (1/8 duty) ⁽⁴⁾		$T_A = -40^{\circ}\text{C}$ to 25°C	3.80	10	
				$T_A = 55^{\circ}\text{C}$	4.30	11	
				$T_A = 85^{\circ}\text{C}$	6.10	16	
				$T_A = 105^{\circ}\text{C}$	10.8	44	
		RTC clocked by LSE external clock (32.768 kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	$T_A = -40^{\circ}\text{C}$ to 25°C	1.50	-	
				$T_A = 55^{\circ}\text{C}$	1.90	-	
				$T_A = 85^{\circ}\text{C}$	3.65	-	
				$T_A = 105^{\circ}\text{C}$	8.25	-	
			LCD ON (static duty) ⁽³⁾	$T_A = -40^{\circ}\text{C}$ to 25°C	1.60	-	
				$T_A = 55^{\circ}\text{C}$	2.05	-	
				$T_A = 85^{\circ}\text{C}$	3.75	-	
				$T_A = 105^{\circ}\text{C}$	8.40	-	
			LCD ON (1/8 duty) ⁽⁴⁾	$T_A = -40^{\circ}\text{C}$ to 25°C	3.90	-	
				$T_A = 55^{\circ}\text{C}$	4.55	-	
				$T_A = 85^{\circ}\text{C}$	6.35	-	
				$T_A = 105^{\circ}\text{C}$	11.10	-	
	RTC clocked by LSE (no independent watchdog) ⁽⁵⁾	LCD OFF		$T_A = -40^{\circ}\text{C}$ to 25°C $V_{DD} = 1.8\text{ V}$	1.23	-	
				$T_A = -40^{\circ}\text{C}$ to 25°C $V_{DD} = 3.0\text{ V}$	1.50	-	
				$T_A = -40^{\circ}\text{C}$ to 25°C $V_{DD} = 3.6\text{ V}$	1.75	-	

Table 26. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	$f_{HCLK} = 32 \text{ MHz}$	0.4	-	μs
$t_{WUSLEEP_LP}$	Wakeup from Low-power sleep mode $f_{HCLK} = 262 \text{ kHz}$	$f_{HCLK} = 262 \text{ kHz}$ Flash enabled	46	-	
		$f_{HCLK} = 262 \text{ kHz}$ Flash switched OFF	46	-	
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$	8.2	-	
		$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage Range 1 and 2	7.7	8.9	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI} = 4.2 \text{ MHz}$ Voltage Range 3	8.2	13.1	
		$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	10.2	13.4	
		$f_{HCLK} = f_{MSI} = 1.05 \text{ MHz}$	16	20	
		$f_{HCLK} = f_{MSI} = 524 \text{ kHz}$	31	37	
		$f_{HCLK} = f_{MSI} = 262 \text{ kHz}$	57	66	
		$f_{HCLK} = f_{MSI} = 131 \text{ kHz}$	112	123	
		$f_{HCLK} = f_{MSI} = 65 \text{ kHz}$	221	236	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	58	104	ms
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI} = 2.1 \text{ MHz}$	2.6	3.25	

1. Guaranteed by characterization results, unless otherwise specified

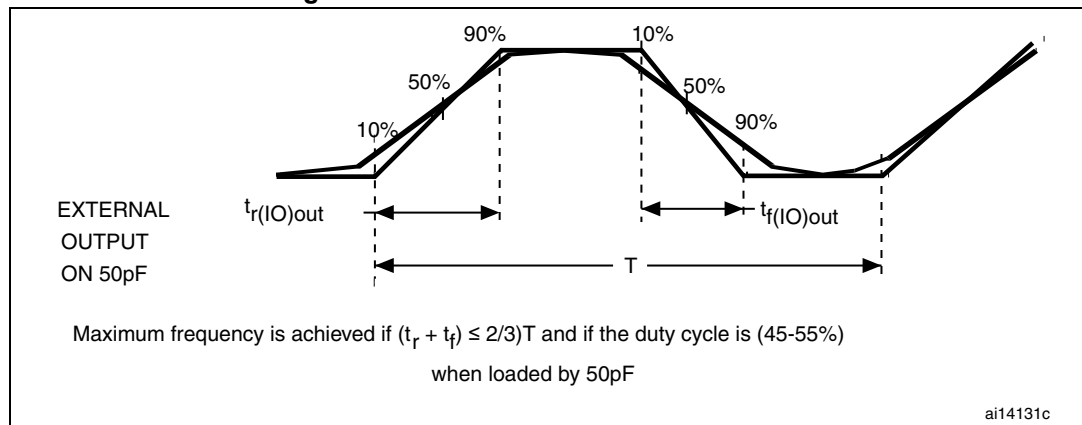
Table 29. HSE oscillator characteristics⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾	$R_S = 30 \Omega$	-	20	-	pF
I_{HSE}	HSE driving current	$V_{DD} = 3.3 \text{ V}$, $V_{IN} = V_{SS}$ with 30 pF load	-	-	3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	$C = 20 \text{ pF}$ $f_{OSC} = 16 \text{ MHz}$	-	-	2.5 (startup) 0.7 (stabilized)	mA
		$C = 10 \text{ pF}$ $f_{OSC} = 16 \text{ MHz}$	-	-	2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	1	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by characterization results.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 17](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 19. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, RPU (see [Table 46](#)).

Unless otherwise specified, the parameters given in [Table 46](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 46. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	-	-	$0.3 V_{DD}$	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	$0.39 V_{DD}+0.59$	-		
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	-	0.4	
		$I_{OL} = 1.5 \text{ mA}$ $1.65 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	-		
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis	-	-	$10\%V_{DD}^{(2)}$		mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_F(NRST)^{(1)}$	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}^{(1)}$	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design.

2. 200 mV minimum value

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#).

Refer to [Section 6.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 50. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	16	MHz
		Slave mode	-	16	
		Slave transmitter	-	12 ⁽³⁾	
$t_{r(SCK)}^{(2)}$ $t_{f(SCK)}^{(2)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode	$4t_{HCLK}$	-	ns
$t_h(NSS)$	NSS hold time	Slave mode	$2t_{HCLK}$	-	
$t_{w(SCKH)}^{(2)}$ $t_{w(SCKL)}^{(2)}$	SCK high and low time	Master mode	$t_{SCK}/2 - 5$	$t_{SCK}/2 + 3$	
$t_{su(MI)}^{(2)}$	Data input setup time	Master mode	5	-	
$t_{su(SI)}^{(2)}$		Slave mode	6	-	
$t_{h(MI)}^{(2)}$	Data input hold time	Master mode	5	-	
$t_{h(SI)}^{(2)}$		Slave mode	5	-	
$t_{a(SO)}^{(4)}$	Data output access time	Slave mode	0	$3t_{HCLK}$	
$t_{v(SO)}^{(2)}$	Data output valid time	Slave mode	-	33	
$t_{v(MO)}^{(2)}$	Data output valid time	Master mode	-	6.5	
$t_{h(SO)}^{(2)}$	Data output hold time	Slave mode	17	-	
$t_{h(MO)}^{(2)}$		Master mode	0.5	-	

1. The characteristics above are given for voltage Range 1.
2. Guaranteed by characterization results.
3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.
4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

Table 52. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage ⁽²⁾	-	3.0	3.6	V
V _{DI} ⁽³⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V _{CM} ⁽³⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽³⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL} ⁽⁴⁾	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾	-	0.3	V
V _{OH} ⁽⁴⁾	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁵⁾	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
3. Guaranteed by characterization results.
4. Guaranteed by test in production.
5. R_L is the load connected on the USB drivers.

Figure 25. USB timings: definition of data signal rise and fall time

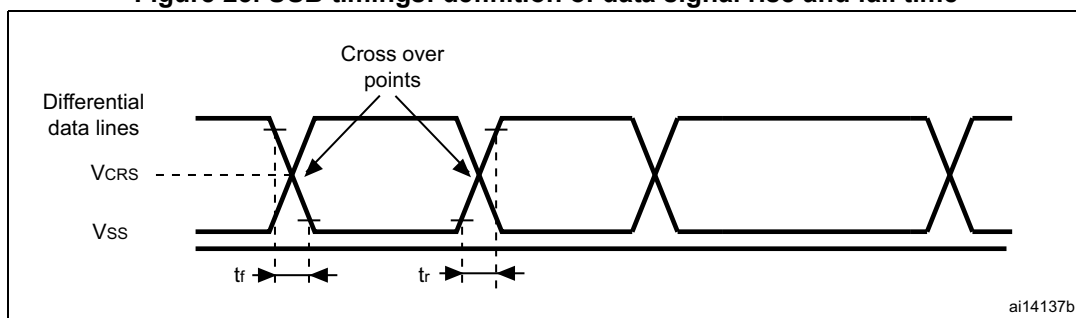


Table 53. USB: full speed electrical characteristics

Driver characteristics ⁽¹⁾					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_f	Fall Time ⁽²⁾	$C_L = 50$ pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification section 7 (version 2.0).

6.3.17 12-bit ADC characteristics

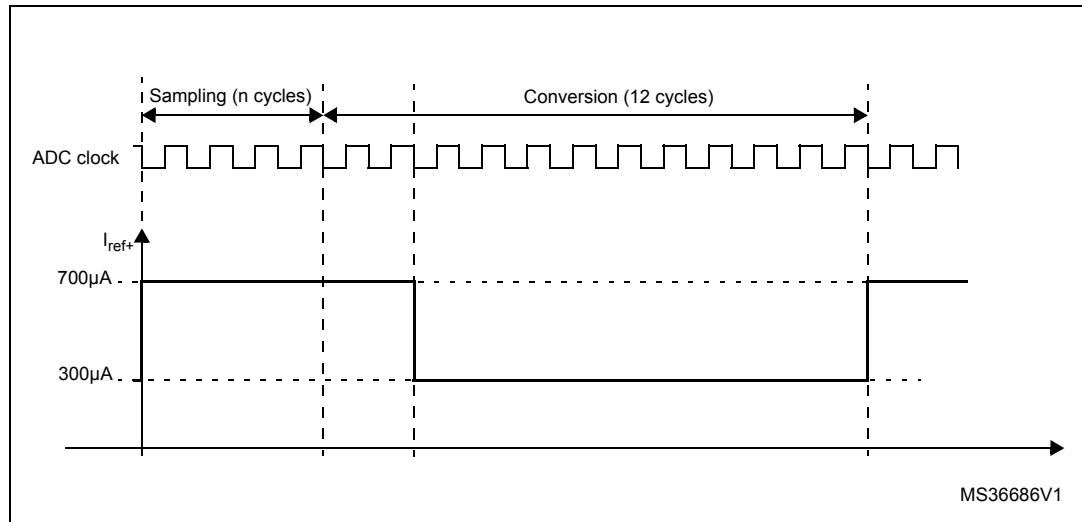
Unless otherwise specified, the parameters given in [Table 55](#) are guaranteed by design.

Table 54. ADC clock frequency

Symbol	Parameter	Conditions			Min	Max	Unit
f _{ADC}	ADC clock frequency	Voltage Range 1 & 2	2.4 V ≤V _{DDA} ≤3.6 V	V _{REF+} = V _{DDA}	0.480	16	MHz
				V _{REF+} < V _{DDA} V _{REF+} > 2.4 V		8	
				V _{REF+} < V _{DDA} V _{REF+} ≤2.4 V		4	
			1.8 V ≤V _{DDA} ≤2.4 V	V _{REF+} = V _{DDA}		8	
				V _{REF+} < V _{DDA}		4	
				Voltage Range 3			

Table 55. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	1.8	-	3.6	V
$V_{\text{REF}+}$	Positive reference voltage	$2.4 \text{ V} \leq V_{\text{DDA}} \leq 3.6 \text{ V}$ $V_{\text{REF}+}$ must be below or equal to V_{DDA}	1.8 ⁽¹⁾	-	V_{DDA}	V
$V_{\text{REF}-}$	Negative reference voltage	-	-	V_{SSA}	-	V
I_{VDDA}	Current on the V_{DDA} input pin	-	-	1000	1450	μA
$I_{\text{VREF}}^{(2)}$	Current on the V_{REF} input pin	Peak	-	400	700	μA
		Average	-		450	μA
V_{AIN}	Conversion voltage range ⁽³⁾	-	0 ⁽⁴⁾	-	$V_{\text{REF}+}$	V
f_{S}	12-bit sampling rate	Direct channels	-	-	1	MSPS
		Multiplexed channels	-	-	0.76	
	10-bit sampling rate	Direct channels	-	-	1.07	MSPS
		Multiplexed channels	-	-	0.8	
	8-bit sampling rate	Direct channels	-	-	1.23	MSPS
		Multiplexed channels	-	-	0.89	
	6-bit sampling rate	Direct channels	-	-	1.45	MSPS
		Multiplexed channels	-	-	1	

Figure 28. Maximum dynamic current consumption on V_{REF+} supply pin during ADC conversion**Table 57. Maximum source impedance $R_{AIN\ max}^{(1)}$**

Ts (μ s)	R _{AIN} max (kOhm)				Ts (cycles) f _{ADC} = 16 MHz ⁽²⁾
	Multiplexed channels		Direct channels		
	2.4 V < V _{DDA} < 3.6 V	1.8 V < V _{DDA} < 2.4 V	2.4 V < V _{DDA} < 3.3 V	1.8 V < V _{DDA} < 2.4 V	
0.25	Not allowed	Not allowed	0.7	Not allowed	4
0.5625	0.8	Not allowed	2.0	1.0	9
1	2.0	0.8	4.0	3.0	16
1.5	3.0	1.8	6.0	4.5	24
3	6.8	4.0	15.0	10.0	48
6	15.0	10.0	30.0	20.0	96
12	32.0	25.0	50.0	40.0	192
24	50.0	50.0	50.0	50.0	384

1. Guaranteed by design.

2. Number of samples calculated for $f_{ADC} = 16\ MHz$. For $f_{ADC} = 8$ and $4\ MHz$ the number of sampling cycles can be reduced with respect to the minimum sampling time Ts (μs).

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 12](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The $100\ nF$ capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

6.3.20 Comparator

Table 61. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V _{DDA}	Analog supply voltage	-	1.65		3.6	V
R _{400K}	R _{400K} value	-	-	400	-	kΩ
R _{10K}	R _{10K} value	-	-	10	-	
V _{IN}	Comparator 1 input voltage range	-	0.6	-	V _{DDA}	V
t _{START}	Comparator startup time	-	-	7	10	μs
t _d	Propagation delay ⁽²⁾	-	-	3	10	
V _{offset}	Comparator offset	-	-	±3	±10	mV
dV _{offset} /dt	Comparator offset variation in worst voltage stress conditions	V _{DDA} = 3.6 V V _{IN+} = 0 V V _{IN-} = V _{REFINT} T _A = 25 °C	0	1.5	10	mV/1000 h
I _{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA

1. Guaranteed by characterization results.

2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

3. Comparator consumption only. Internal reference voltage not included.

Figure 48. Thermal resistance suffix 6

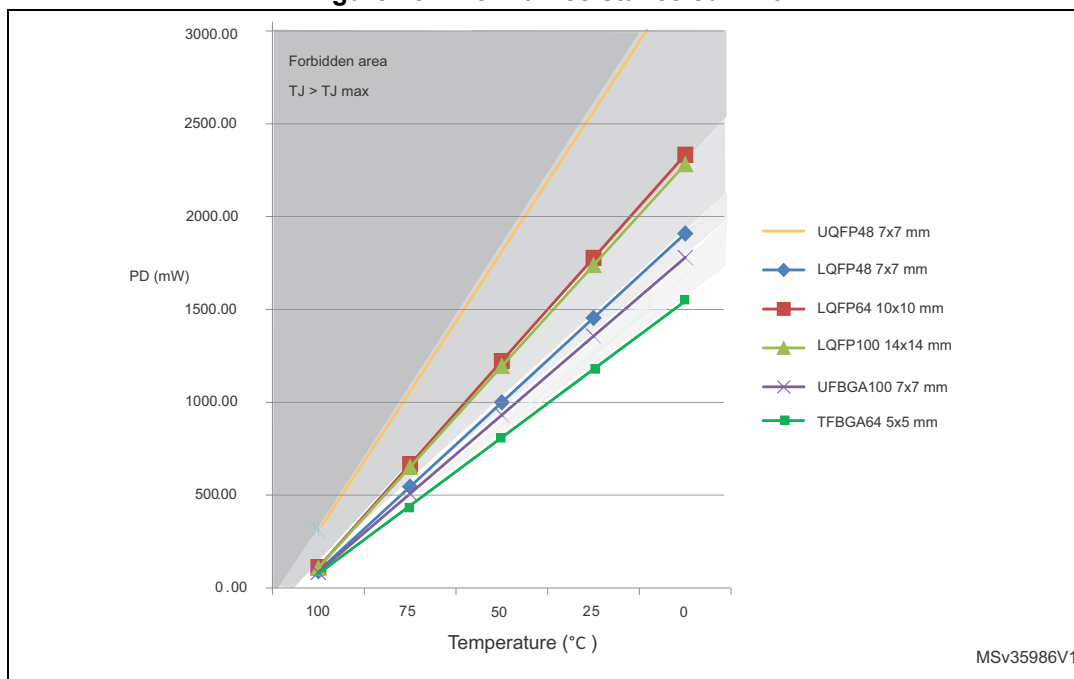
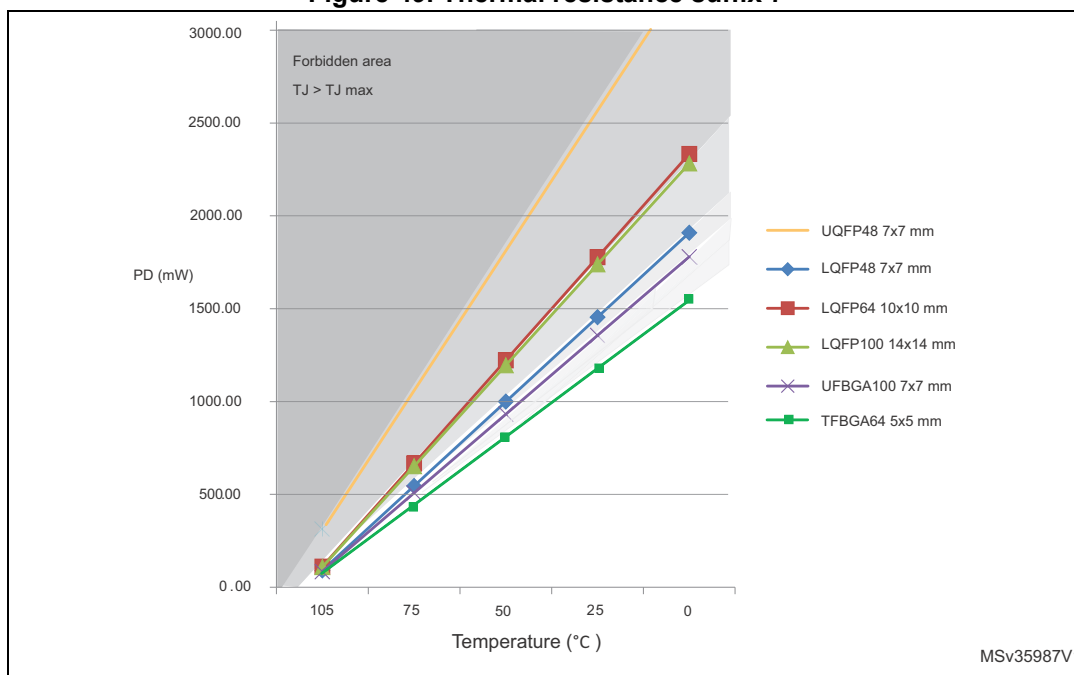


Figure 49. Thermal resistance suffix 7



7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.